

Protection Device

TVS (Transient Voltage Suppressor)

ESD113-B1 Series

Bi-directional, 3.6 V, 0.2 pF, 0201, 0402, RoHS and Halogen Free compliant

ESD113-B1-02ELS
ESD113-B1-02EL

Data Sheet

Revision 1.2, 2014-05-14
Final

Power Management & Multimarket

Edition 2014-05-14

**Published by
Infineon Technologies AG
81726 Munich, Germany
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1 Product Overview

1.1 Features

- ESD / transient protection of high speed data lines according to:
 - IEC61000-4-2 (ESD): ± 20 kV (air / contact)
 - IEC61000-4-4 (EFT): ± 2.5 kV / ± 50 A (5/50 ns)
 - IEC61000-4-5 (surge): ± 3 A (8/20 μ s)
- Bi-directional, working voltage up to: $V_{RWM} = \pm 3.6$ V
- Ultra low capacitance $C_L = 0.20$ pF (typical) at $f = 1$ GHz
- Very low clamping voltage: $V_{CL} = 14$ V (typical) at $I_{TLP} = 16$ A
- Very low reverse current. $I_R < 1$ nA (typical)
- Very low dynamic resistance: $R_{DYN} = 0.45$ Ω (typical)
- Pb-free and halogen-free package (RoHS compliant)



1.2 Application Examples

- USB 3.0, Firewire, DVI, HDMI, S-ATA, DisplayPort, Thunderbolt
- Mobile HDMI Link, MDDI, MIPI, SWP / NFC

1.3 Product Description

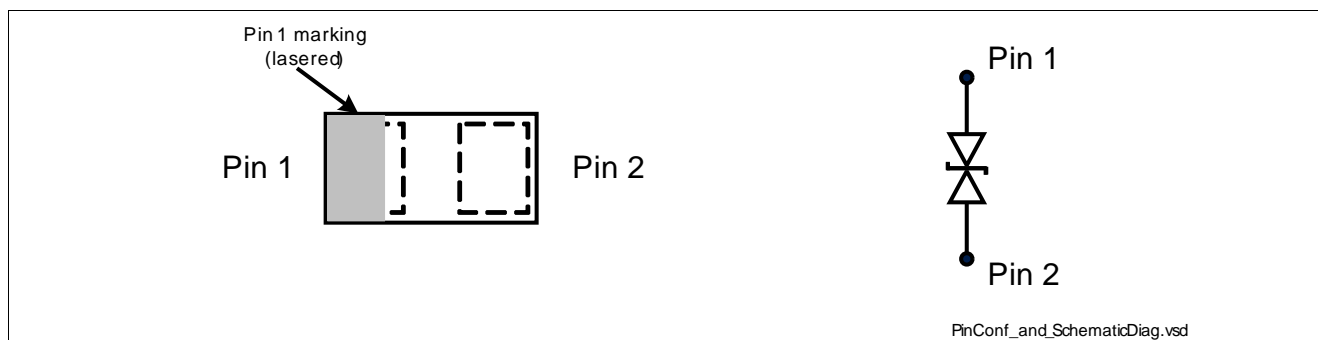


Figure 1-1 Pin Configuration and Schematic Diagram

Table 1-1 Part Information

Type	Package	Configuration	Marking code
ESD113-B1-02ELS	TSSLP-2-4	1 line, bi-directional	<u>2</u>
ESD113-B1-02EL	TSLP-2-20	1 line, bi-directional	CC

2 Maximum Ratings

Table 2-1 Maximum Rating at $T_A = 25\text{ °C}$, unless otherwise specified¹⁾

Parameter	Symbol	Values	Unit
ESD air discharge ²⁾	V_{ESD}	± 20	kV
ESD contact discharge ²⁾		± 20	
Peak pulse power	P_{PK}	36	W
Peak pulse current ³⁾	I_{PP}	± 3	A
Operating temperature	T_{OP}	-55 to 125	°C
Storage temperature	T_{stg}	-65 to 150	°C

1) Device is electrically symmetrical

2) V_{ESD} according to IEC61000-4-2

3) Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5

Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the component.

3 Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

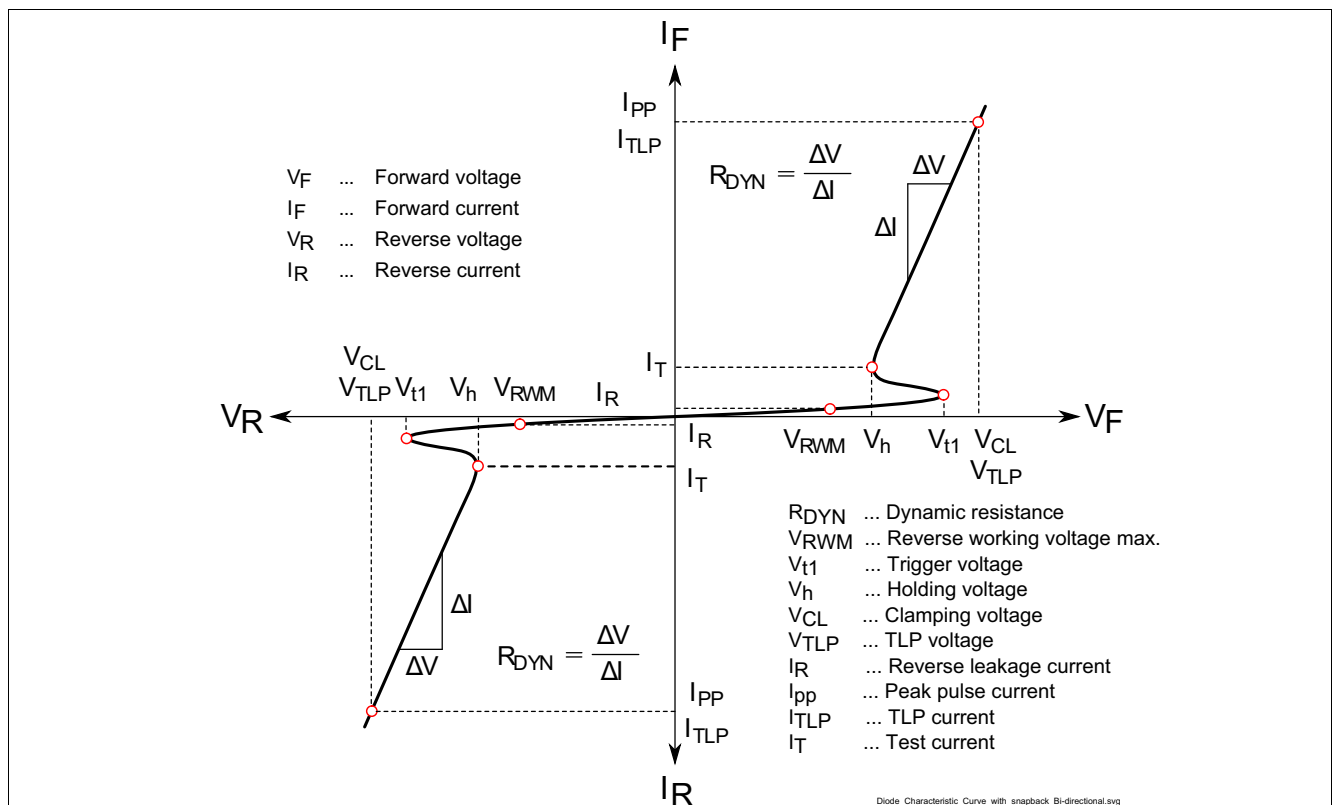


Figure 3-1 Definitions of electrical characteristics

Electrical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified
Table 3-1 DC Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified ¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Reverse working voltage	V_{RWM}	-3.6	—	3.6	V	
Trigger voltage	V_{t1}	4	—	—		
Holding voltage	V_h	4	4.6	5.5		$I_T = 10\text{ mA}$
Reverse leakage current	I_R	—	<1	20	nA	$V_R = 3.3\text{ V}$

1) Device is electrically symmetrical

Table 3-2 AC Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Line capacitance	C_L	—	0.2	0.35	pF	$V_R = 0\text{ V}, f = 1\text{ MHz}$
		—	0.2	—		$V_R = 0\text{ V}, f = 1\text{ GHz}$
Series inductance	L_S	—	0.2	—	nH	ESD113-B1-02ELS
		—	0.4	—		ESD113-B1-02EL

Table 3-3 ESD and Surge Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified ¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Clamping voltage ²⁾	V _{CL}	—	14	—	V	I _{TLP} = 16 A, t _p = 100 ns
		—	20	—		I _{TLP} = 30 A, t _p = 100 ns
Clamping voltage ³⁾		—	6	—		I _{PP} = 1 A, t _p = 8/20 μs
		—	8	—		I _{PP} = 3 A, t _p = 8/20 μs
Dynamic resistance ²⁾	R _{DYN}	—	0.45	—	Ω	t _p = 100 ns

1) Device is electrically symmetrical

2) Please refer to Application Note AN210[1]. TLP parameter: $Z_0 = 50\text{ }\Omega$, $t_p = 100\text{ ns}$, $t_r = 300\text{ ps}$.

3) Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5

4 Typical Characteristics Diagrams

Typical characteristics diagrams at $T_A=25^\circ\text{C}$, unless otherwise specified

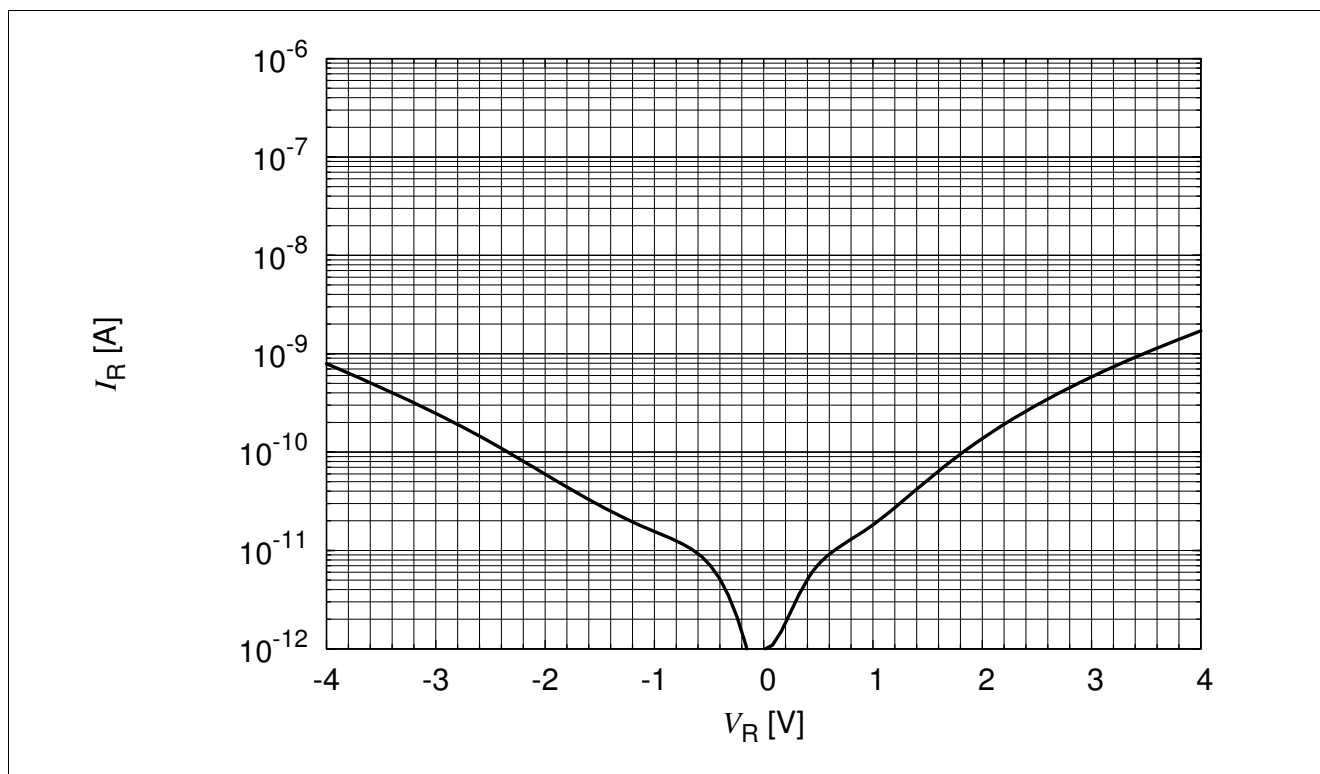


Figure 4-1 Reverse leakage current $I_R = f(V_R)$

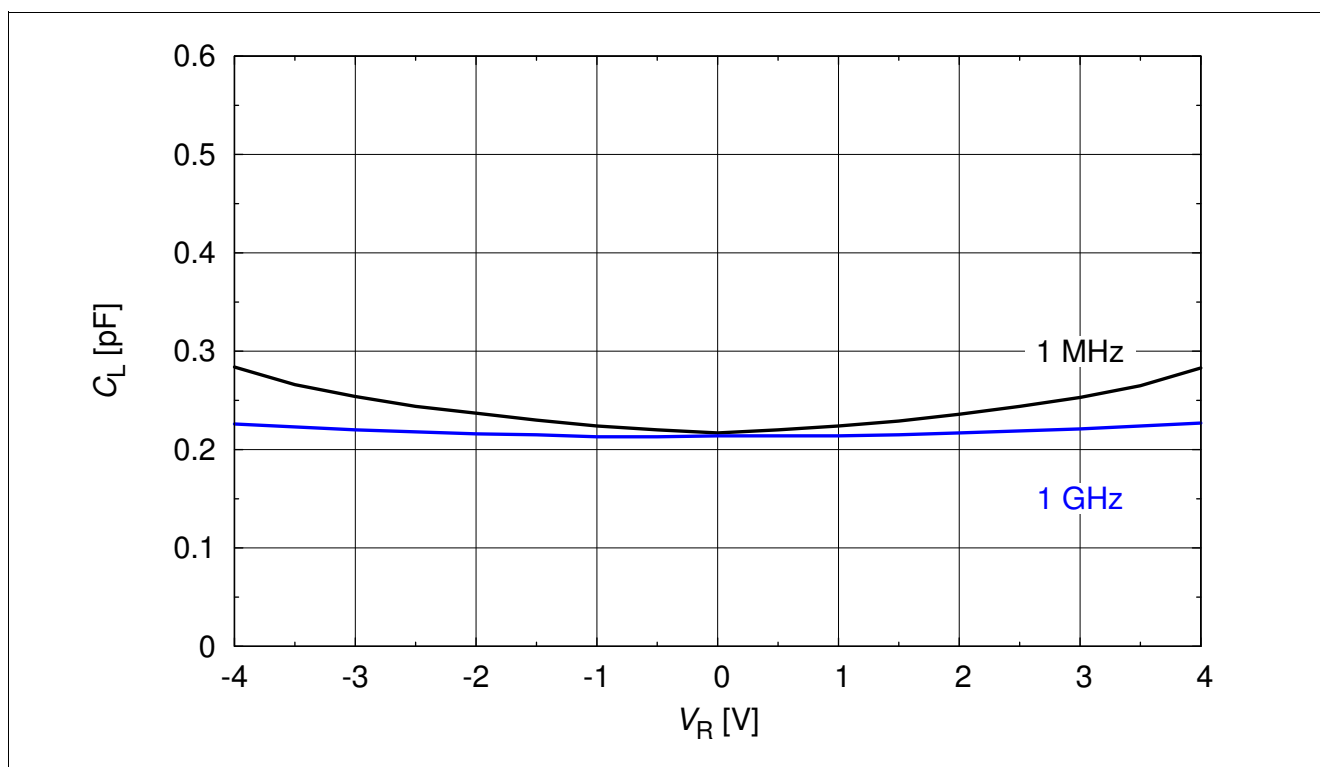


Figure 4-2 Line capacitance $C_L = f(V_R)$

Typical Characteristics Diagrams

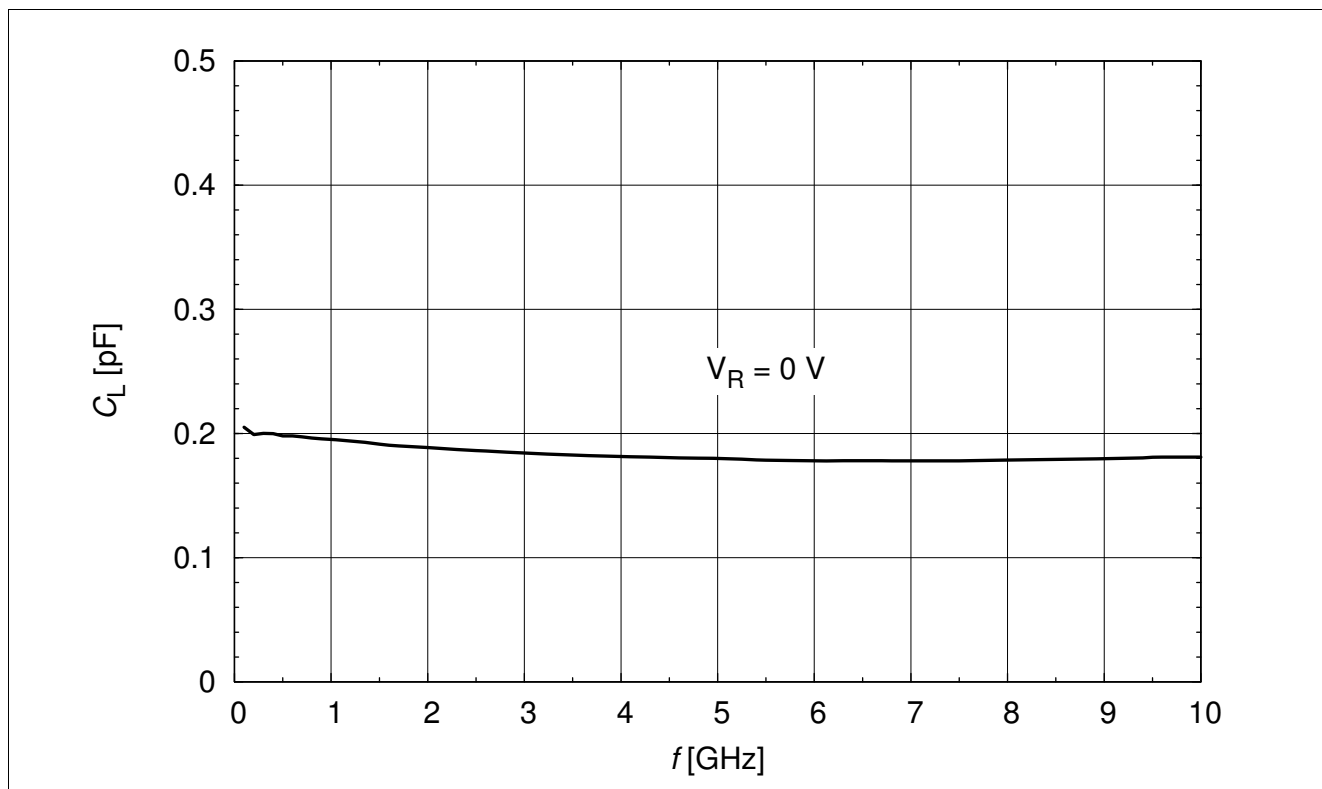


Figure 4-3 Line capacitance: $C_L = f(f)$, $V_R = 0$ V

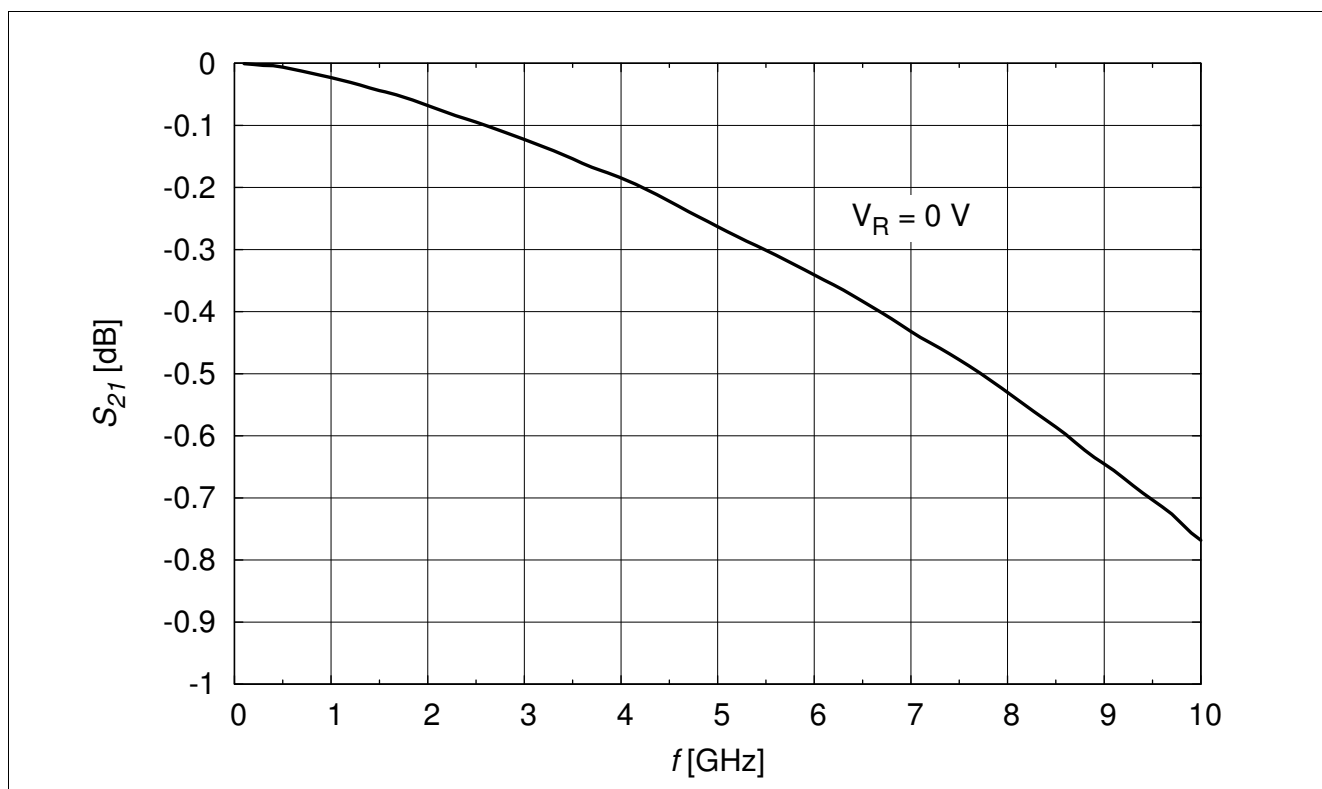


Figure 4-4 Insertion loss vs. frequency in a 50 Ω system

Typical Characteristics Diagrams

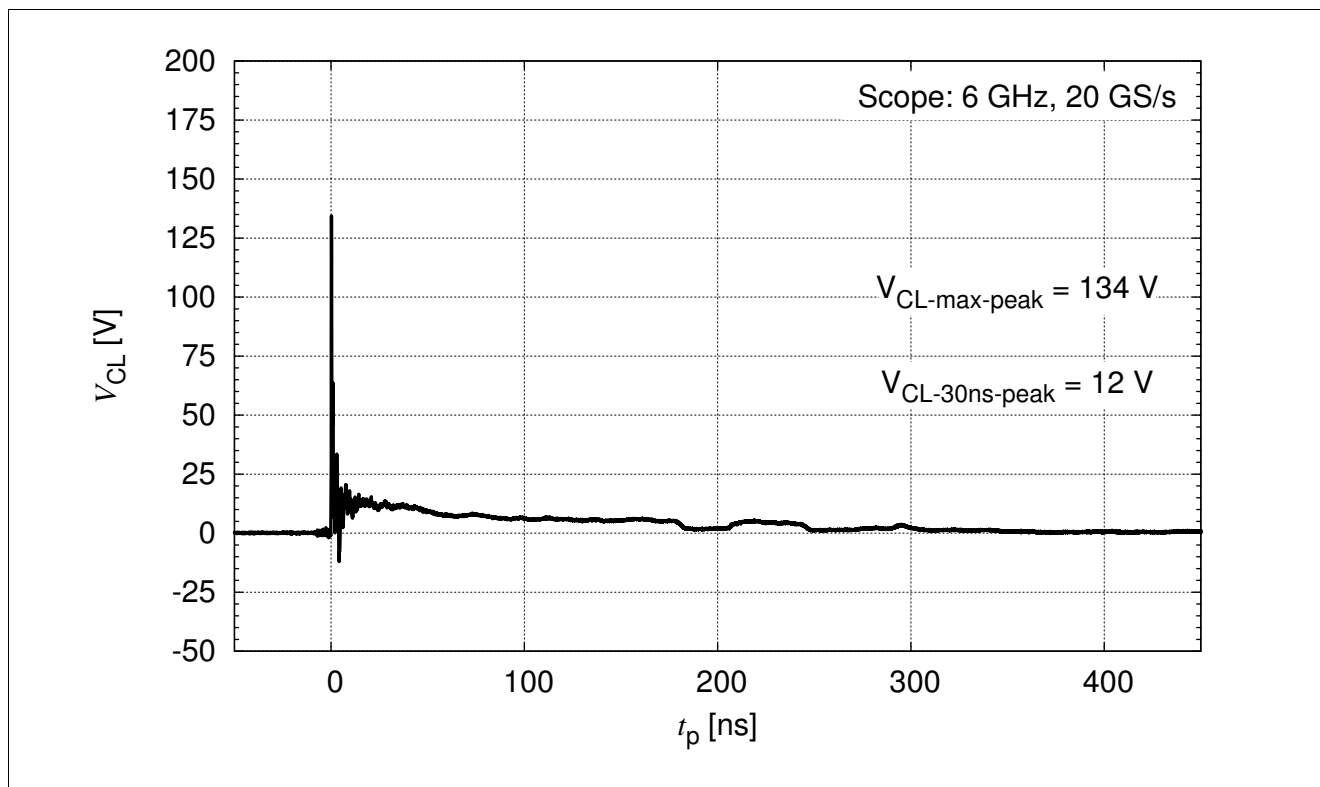


Figure 4-5 Clamping voltage (ESD): $V_{CL} = f(t)$, 8 kV positiv pulse from pin 1 to pin 2

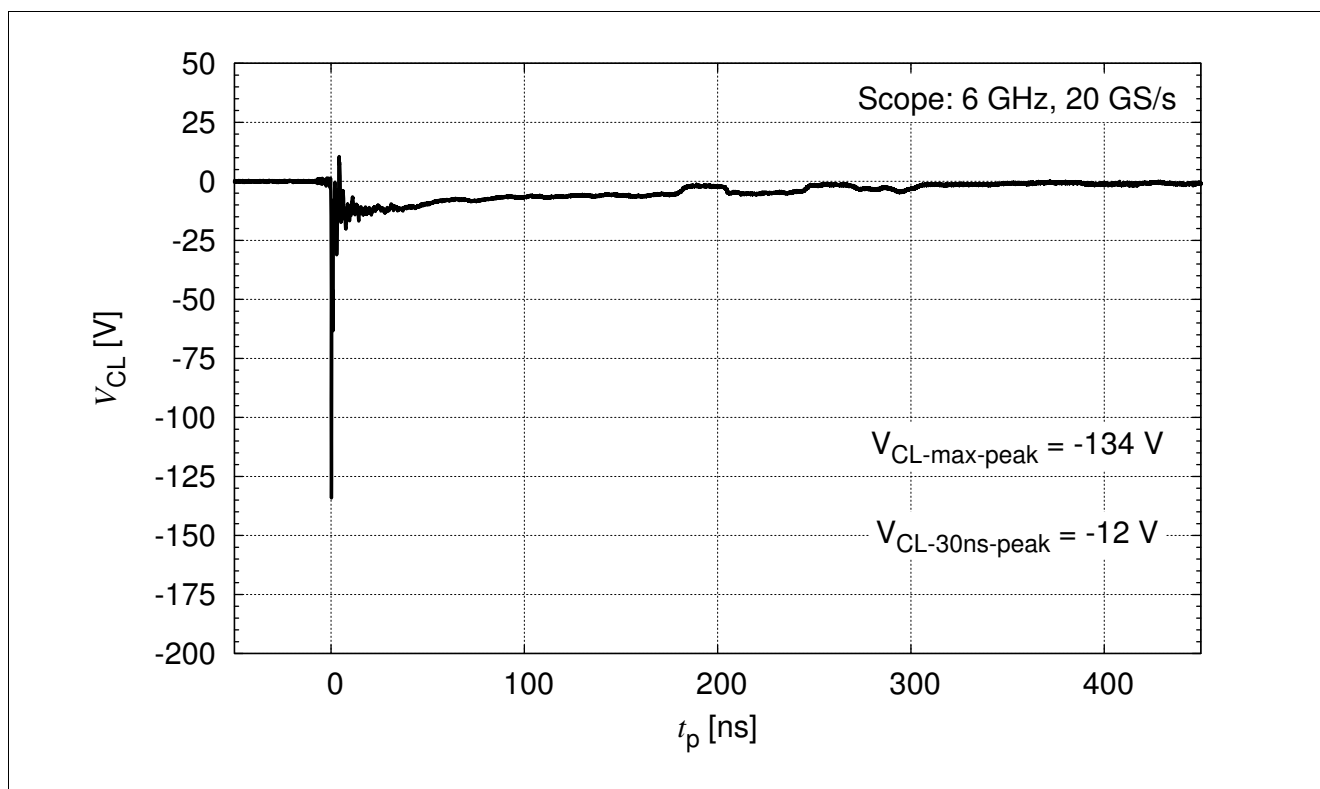


Figure 4-6 Clamping voltage (ESD): $V_{CL} = f(t)$, 8 kV negativ pulse from pin 1 to pin 2

Typical Characteristics Diagrams

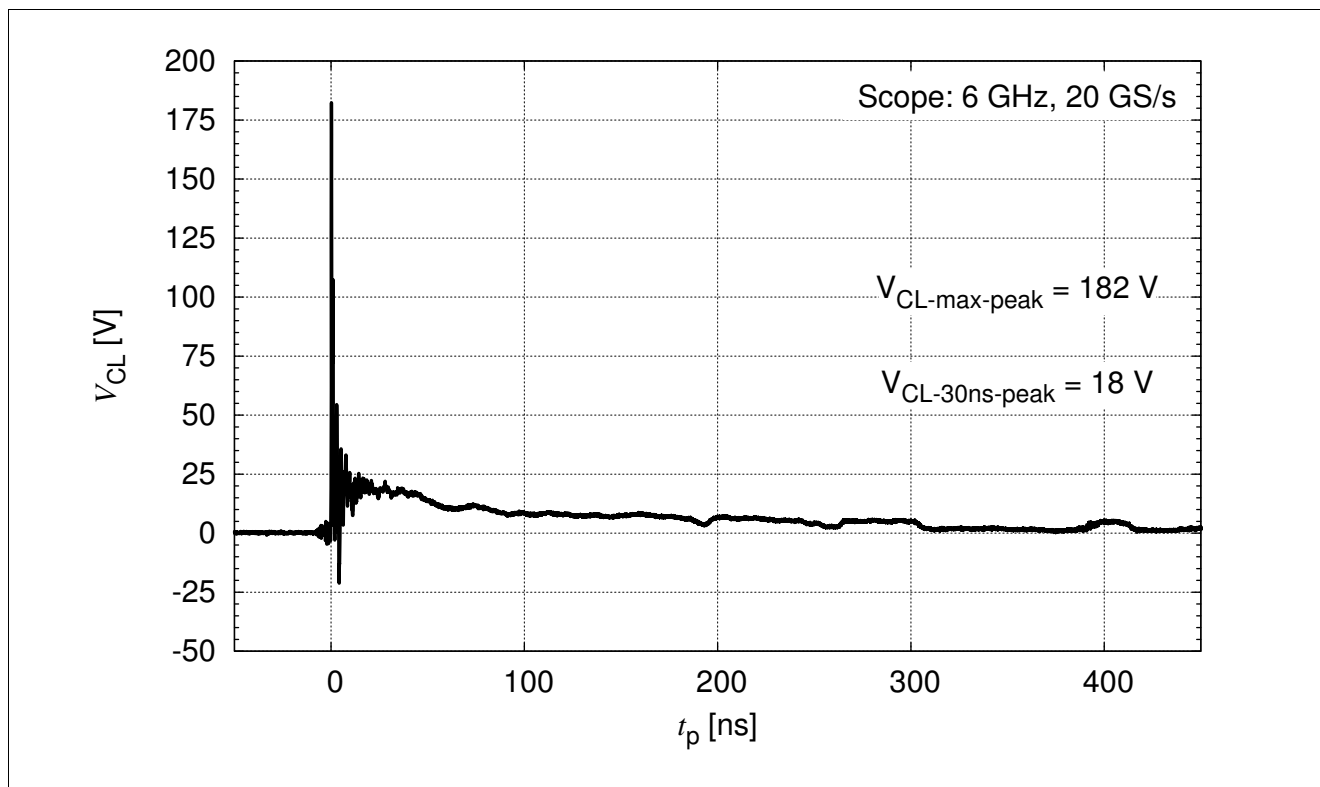


Figure 4-7 Clamping voltage (ESD): $V_{CL} = f(t)$, 15 kV positiv pulse from pin 1 to pin 2

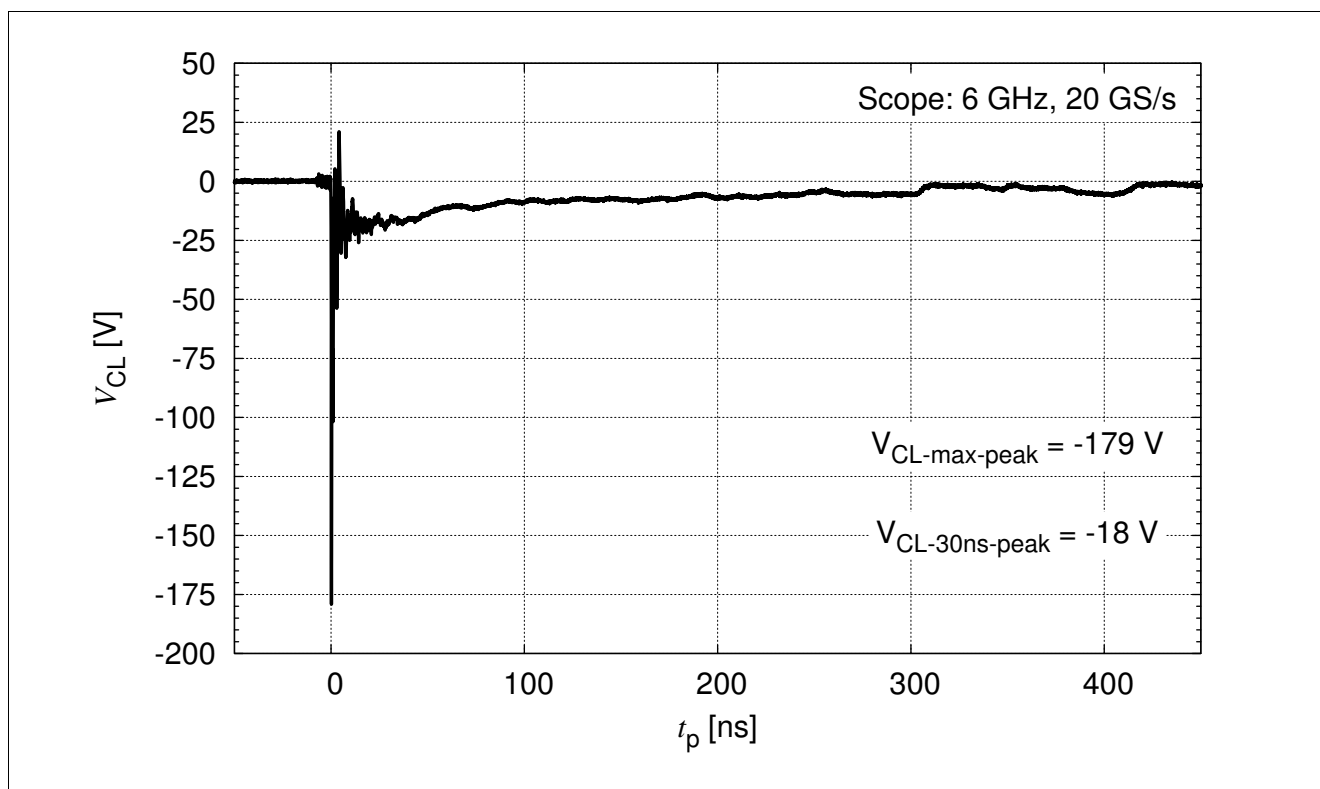


Figure 4-8 Clamping voltage (ESD): $V_{CL} = f(t)$, 15 kV negativ pulse from pin 1 to pin 2

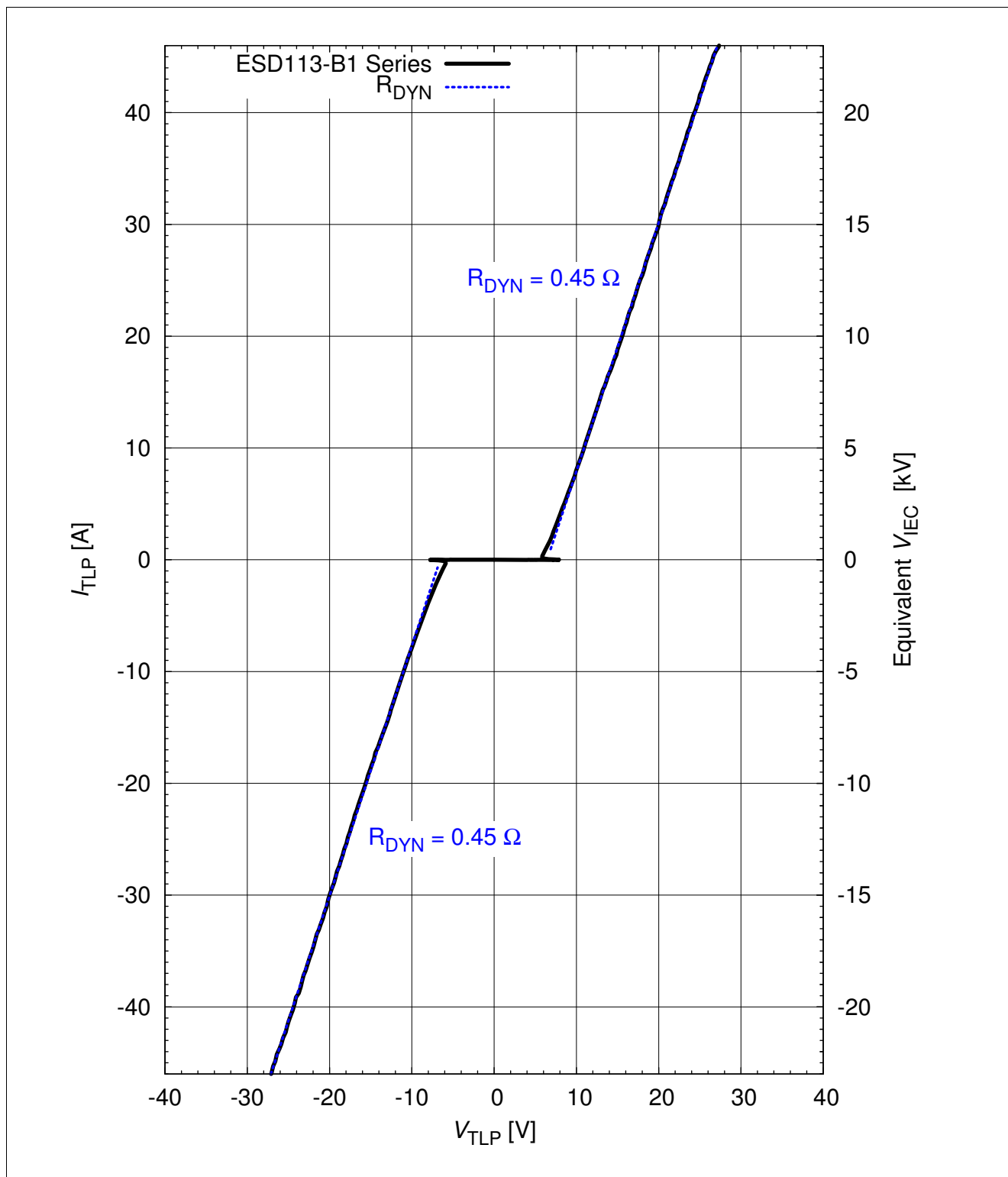


Figure 4-9 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$ [1], pin 1 to pin 2

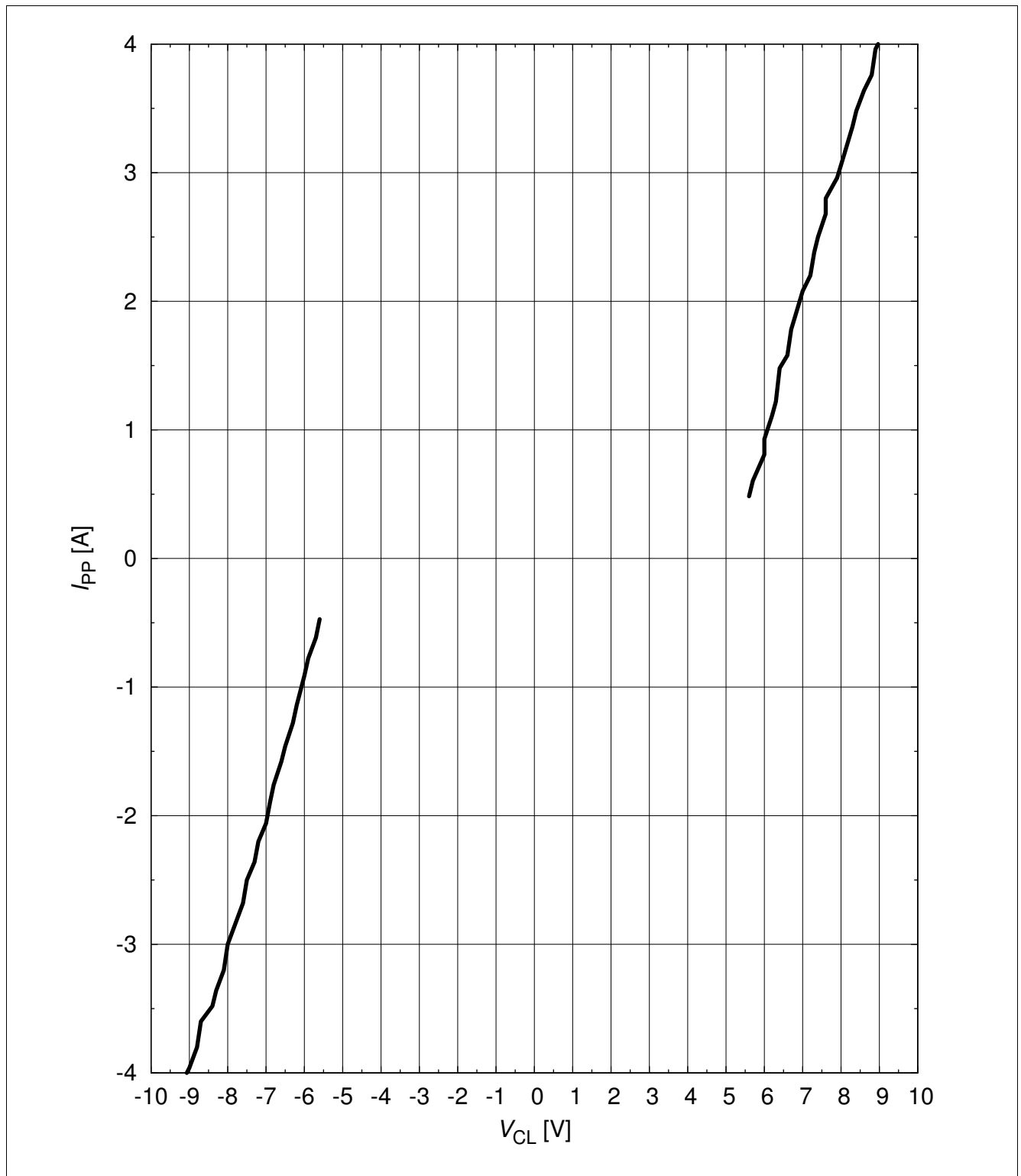


Figure 4-10 Clamping voltage (Surge): $I_{PP} = f(V_{CL})$ [1], pin 1 to pin 2

5 Package Information

5.1 TSSLP-2-4

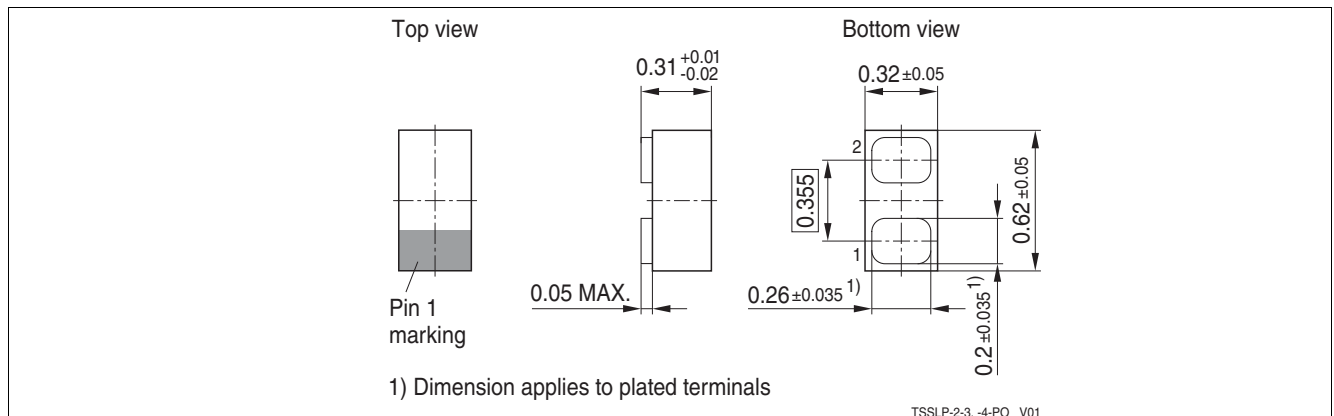


Figure 5-1 TSSLP-2-4 Package outline (dimension in mm)

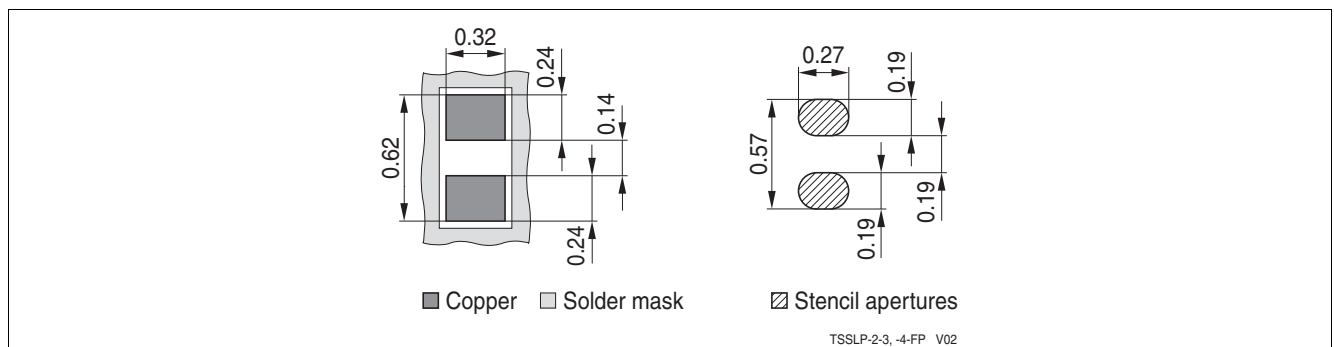


Figure 5-2 TSSLP-2-4 Footprint (dimension in mm)

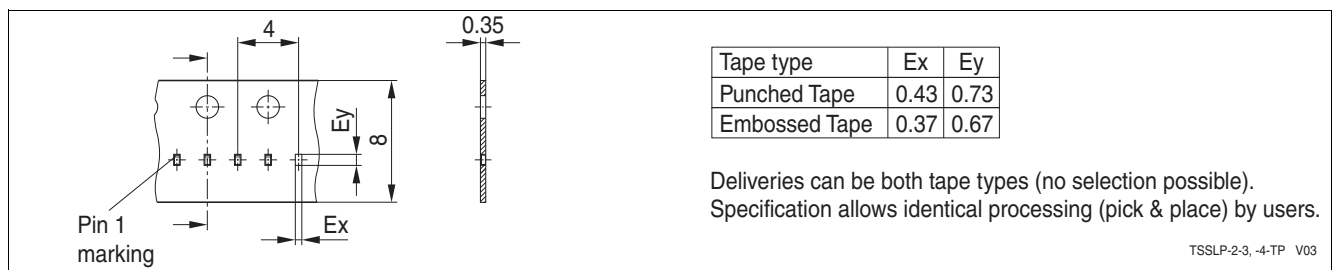


Figure 5-3 TSSLP-2-4 Packing (dimension in mm)

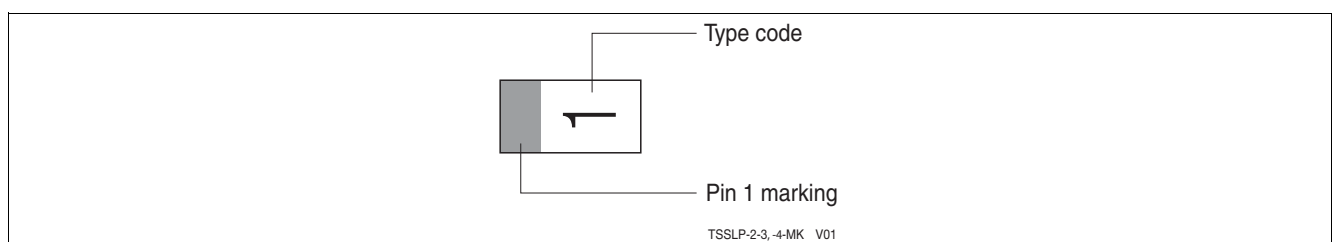


Figure 5-4 TSSLP-2-4 Marking example [Table 1-1 "Part Information" on Page 3](#)

5.2 TSLP-2-20

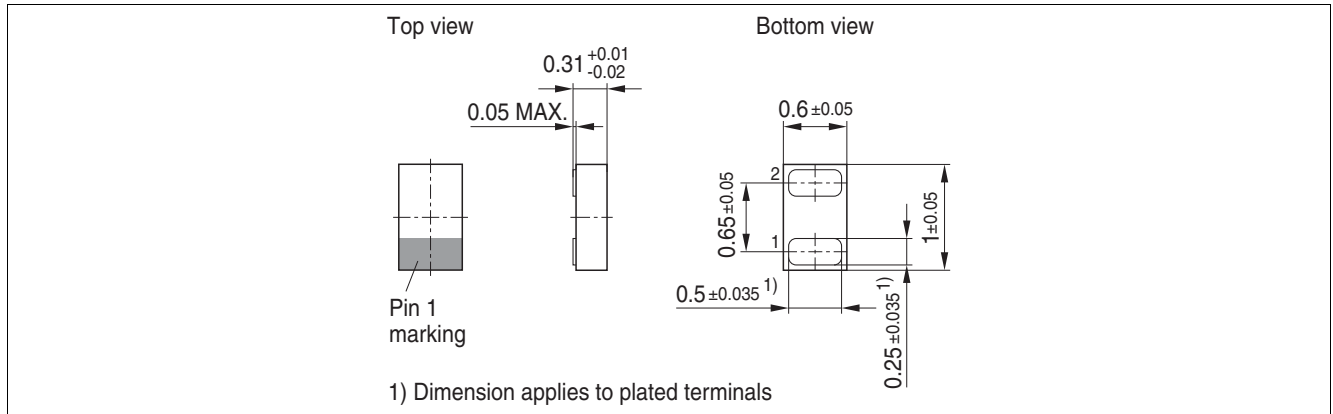


Figure 5-5 TSLP-2-20 Package outline (dimension in mm)

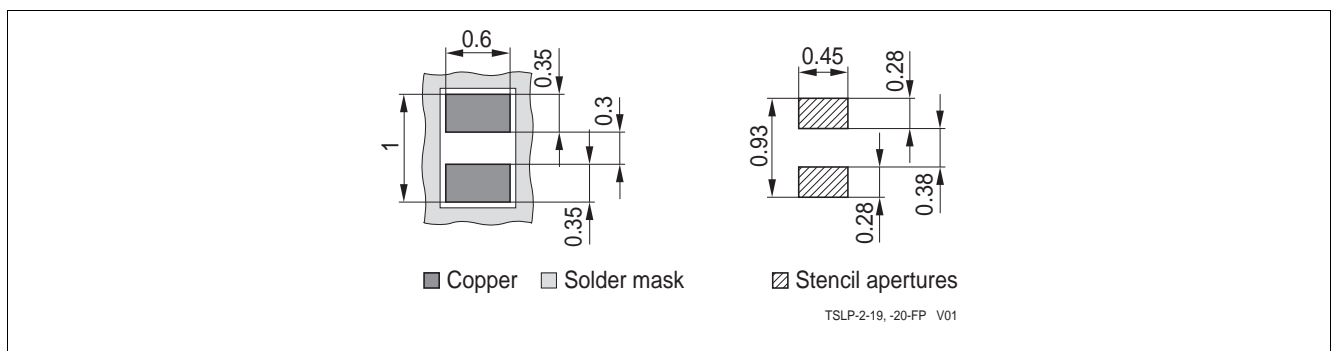


Figure 5-6 TSLP-2-20 Footprint (dimension in mm)

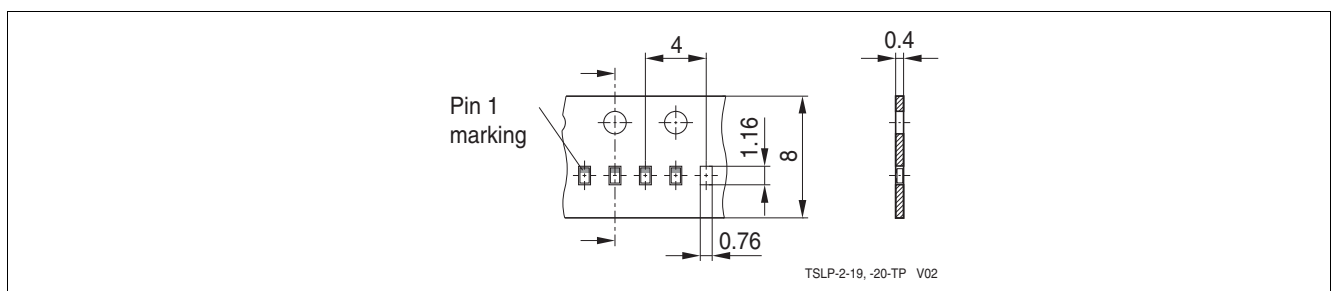


Figure 5-7 TSLP-2-20 Packing (dimension in mm)

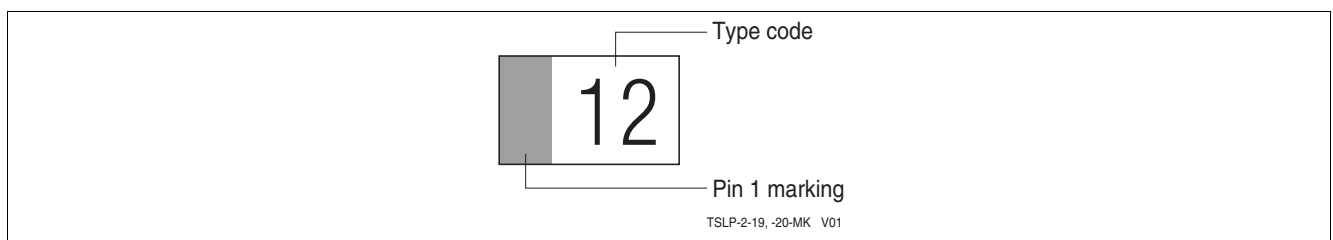


Figure 5-8 TSSLP-2-4 Marking example [Table 1-1 "Part Information" on Page 3](#)

References

- [1] Infineon AG - **Application Note AN210**: Effective ESD Protection Design at System Level Using VF-TLP Characterization Methodology
- [2] Infineon AG - Recommendations for PCB Assembly of Infineon TSLP and TSSLP Package

Revision History: Rev.1.1, 2013-02-06

Page or Item	Subjects (major changes since previous revision)
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Revision 1.2, 2014-05-14

All	New type ESD113-B1-02EL inserted

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